

<b>PCN Number:</b>	20200309001.2		<b>PCN Date:</b>	Mar. 31, 2020	
<b>Title:</b>	Qualify UMC-F12 for c021.A Process as alternate source				
<b>Customer Contact:</b>	<a href="#">PCN Manager</a>			<b>Dept:</b>	Quality Services
<b>Proposed 1<sup>st</sup> Ship Date:</b>	Oct. 1, 2020	<b>Estimated Sample Availability:</b>		Date provided at sample request	
<b>Change Type:</b>					
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Site
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Material
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input type="checkbox"/>	Wafer Bump Process
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input checked="" type="checkbox"/>	Wafer Fab Site
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input checked="" type="checkbox"/>	Wafer Fab Materials
		<input type="checkbox"/>		<input type="checkbox"/>	Wafer Fab Process
<b>PCN Details</b>					
<b>Description of Change:</b>					
Texas Instruments Incorporated is announcing the qualification of Wafer Fab site UMC-F12 in the c021.A process as an alternate source.					
<b>Current Fab Site</b>			<b>Alternate Fab Site</b>		
<b>Current Fab Site</b>	<b>Process</b>	<b>Wafer Diameter</b>	<b>New Fab Site</b>	<b>Process</b>	<b>Wafer Diameter</b>
DMOS6	c021.A	300 mm	UMC-F12	c021.A	300 mm
<b>Description</b>		<b>Current Fab</b>	<b>Alternate Fab</b>		
Gate Oxide Material		Nitrided Thin Gate Oxide	SiO2		
Dielectric Material		OSG/FSG/TEOS	LK SiOC (K value = 3.1)		
Metallization material, front or back side		Copper Interconnect	Front side. Interconnection: Copper RDL (Re-distribution Layer): Aluminum		
Contact		NiPt	W fill with TiN barrier		
Contact Via Plug		Tungsten	Cu fill with Ta barrier		
Top protective layer or Passivation layer material		PO Oxide (TEOS/SiON)	SiN		
<b>Reason for Change:</b>					
Qualify c021.A to UMC-F12 as alternate source.					
<b>Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):</b>					
None					
<b>Changes to product identification resulting from this PCN:</b>					
<b>Current:</b>					
Current Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City		
DMOS6	DM6	USA	Dallas		
<b>New Fab Site:</b>					
New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City		
<b>UMC-F12</b>	<b>F12</b>	<b>TWN</b>	<b>Tainan</b>		

**Sample Product Shipping Label (not actual product label)**

TEXAS INSTRUMENTS  
MADE IN: Malaysia  
2DC: 2Q:



(1P) SN74LS07NSR  
(Q) 2000 (D) 0336  
(31T) LOT: 3959047MLA  
(4W) TKY (1T) 7523483SI2  
(P)  
(2P) REV: (V) 0033317  
(20L) CSO: SHE (21L) CCO: USA  
(22L) ASO: MLA (23L) ACO: MYS

MSL '2 /260C/1 YEAR	SEAL DT
MSL 1 /235C/UNLIM	03/29/04

OPT:  
ITEM: 39  
LBL: 5A (L) TO: 1750

**Product Affected:**

DS90UB964TRGCRQ1  
DS90UB964TRGCTQ1

**Automotive New Product Qualification Summary**  
(As per AEC-Q100 and JEDEC Guidelines)  
**Approved 14-January-2020**

**Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: DS90UB964TRGCRQ1
<b>Test Group A – Accelerated Environment Stress Tests</b>							
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 110C/85%RH	264 Hours	3/231/0
UHAST	A3	JEDEC JESD22-A118	3	77	Unbiased HAST, 110C/85%RH	264 Hours	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	30	Post Temp Cycle Bond Pull	Wires	3/90/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp Storage Bake 150C	1000 Hours	1/45/0
<b>Test Group B – Accelerated Lifetime Simulation Tests</b>							
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 125C	1000 Hours	3/231/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	3/2400/0
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A
<b>Test Group C – Package Assembly Integrity Tests</b>							
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear (Cpk>1.67)	Wires	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	3/30/0
LI	C6	JEDEC JESD22-B105	1	50	Lead Integrity	-	N/A
<b>Test Group D – Die Fabrication Reliability Tests</b>							
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements
TDDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: DS90UB964TRGCRQ1
<b>Test Group E – Electrical Verification Tests</b>							
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	4000 V All pins	1/3/0
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	8000V RIn+[3:0] and RIN-[3:0] pins	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1000 V	1/3/0
LU	E4	AEC Q100-004	1	6	Auto Latch-up	Ta(max)	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67	3/90/0

**A1 (PC): Preconditioning:**

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

**Ambient Operating Temperature by Automotive Grade Level:**

Grade 0 (or E): -40°C to +150°C

Grade 1 (or Q): -40°C to +125°C

Grade 2 (or T): -40°C to +105°C

Grade 3 (or I): -40°C to +85°C

**E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):**

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

**Green/Pb-free Status:**

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

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